



FH1100

SILICON DIODE

DESCRIPTION:

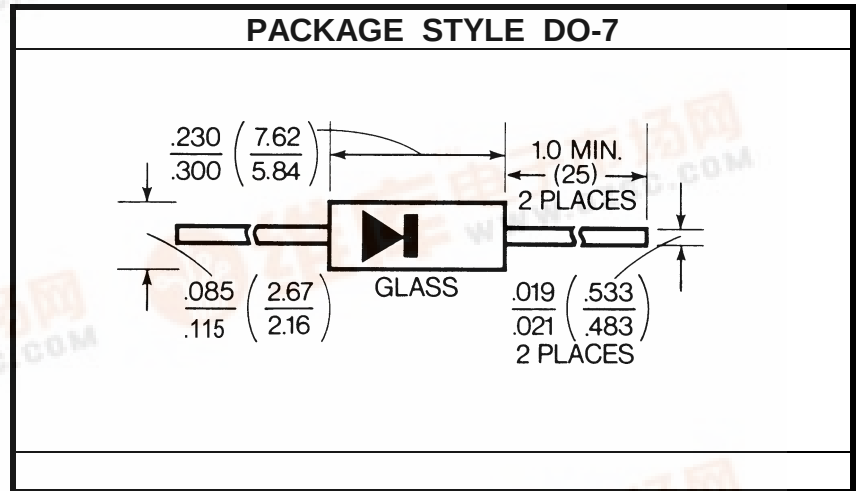
The **ASI FH1100** is a Silicon Diffused Hot Carrier Diode.

FEATURES INCLUDE:

- $Q_S = 1.6$ pC Typ.
- $C = 1.0$ pF Max. @ $f = 890$ MHz
- Hermetic Glass Package

MAXIMUM RATINGS

I_F	10 mA
V_R	5.0 V
P_{DISS}	100 mW @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+125^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
$T_{soldering}$	$+260^\circ\text{C}$ for 5 Seconds



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_F	$I_F = 10$ mA			550	mV
I_R	$V_R = 1.0$ V			1.0	μA
V_{BR}	$I_R = 100$ μA	5.0			V
C_{T0}	$V_R = 0$ V $f = 1.0$ MHz		1.0		pF
NF	$f = 890$ MHz			10	dB
Q_S	$I_F = 10$ mA		1.6		pC

